

Features

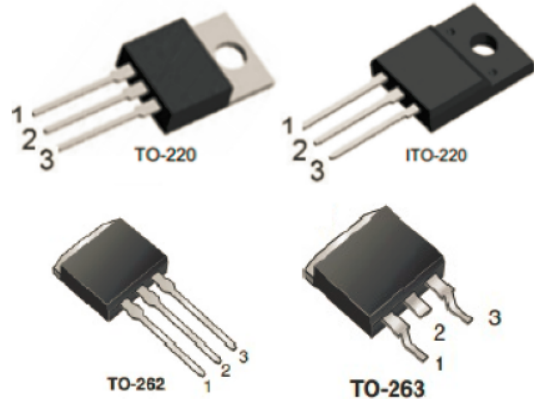
- $R_{DS(ON)} < 1.5\Omega$ @ $V_{GS} = 10V$
- Fast switching capability
- Low gate charge
- Lead free in compliance with EU RoHS directive.
- Green molding compound

PRODUCT SUMMARY

V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)
650	1.5 @ $V_{GS} = 10V$	7

Pin Definition:

1. Gate
2. Drain
3. Source



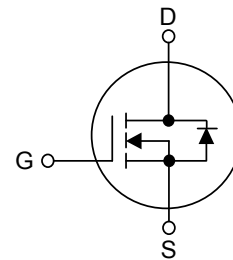
Mechanical Data

- Case: TO-220, ITO-220, TO-262, TO-263 Package

Ordering Information

Part No.	Package	Packing
DMT7N65-TU	TO-220	50pcs / Tube
DMF7N65-TU	ITO-220	50pcs / Tube
DMK7N65-TU	TO-262	50pcs / Tube
DMG7N65-TU	TO-263	50pcs / Tube
DMG7N65-TR	TO-263	800pcs / 13" Reel

Block Diagram



ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ C$, unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT	
Drain-Source Voltage	V_{DSS}	650	V	
Gate-Source Voltage	V_{GSS}	± 30	V	
Continuous Drain Current	I_D	7	A	
Pulsed Drain Current (Note 2)	I_{DM}	28	A	
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	435	mJ
Power Dissipation	TO-220/TO-262/TO-263	P_D	142	W
	ITO-220		48	W
Junction Temperature	T_J	+150	$^\circ C$	
Storage Temperature	T_{STG}	-55 ~ +150	$^\circ C$	

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating : Pulse width limited by T_J

3. $L = 30mH$, $I_{AS} = 5.25A$, $V_{DD} = 50V$, $R_G = 25 \Omega$, Starting $T_J = 25^\circ C$

THERMAL DATA

PARAMETER		SYMBOL	RATING	UNIT
Junction to Ambient	TO-220/ITO-220 TO-262/TO-263	θ_{JA}	62.5	°C/W
Junction to Case	TO-220/TO-262/TO-263	θ_{JC}	0.90	°C/W
	ITO-220		2.6	

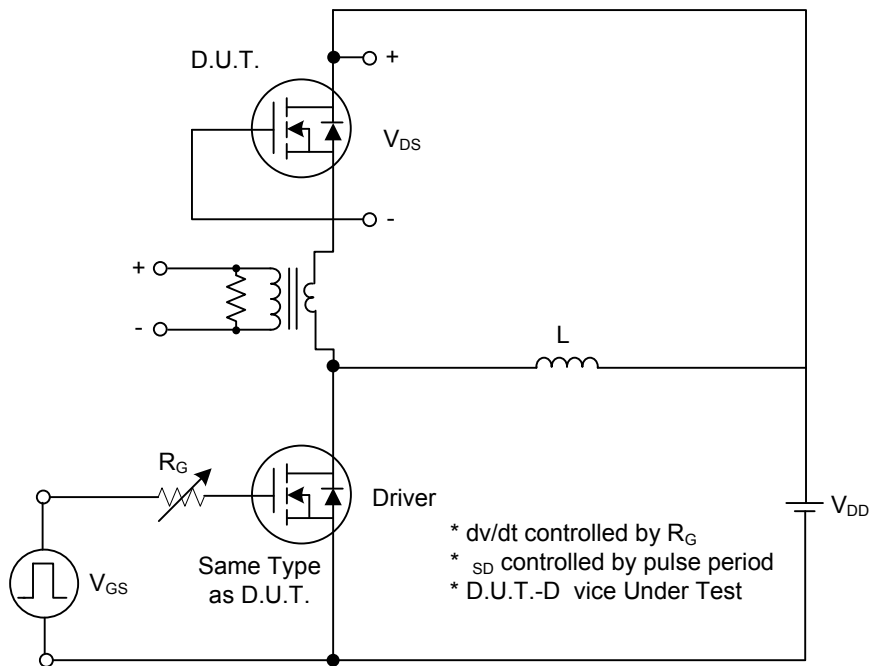
ELECTRICAL CHARACTERISTICS (T_C=25°C, unless otherwise specified)

PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV _{DSS}	V _{GS} =0V, I _D =250μA	650			V
Drain-Source Leakage Current		I _{DSS}	V _{DS} =650V, V _{GS} =0V			1	μA
Gate- Source Leakage Current	Forward	I _{GSS}	V _{GS} =30V, V _{DS} =0V			100	nA
	Reverse		V _{GS} =-30V, V _{DS} =0V			-100	nA
Breakdown Voltage Temperature Coefficient		$\Delta BV_{DSS}/\Delta T_J$	I _D =250μA, Referenced to 25°C		0.67		V/°C
ON CHARACTERISTICS							
Gate Threshold Voltage		V _{GS(TH)}	V _{DS} =V _{GS} , I _D =250μA	2.0		4.0	V
Static Drain-Source On-State Resistance		R _{DS(ON)}	V _{GS} = 10V, I _D = 3.5A		1.35	1.5	Ω
DYNAMIC CHARACTERISTICS							
Input Capacitance		C _{ISS}	V _{DS} =25V, V _{GS} =0V, f=1.0 MHz		1210	1400	pF
Output Capacitance		C _{OSS}			140	180	pF
Reverse Transfer Capacitance		C _{RSS}			40	50	pF
SWITCHING CHARACTERISTICS							
Turn-On Delay Time		t _{D(ON)}	V _{DD} =300V, I _D =7A, R _G =25Ω (Note 1, 2)		50	70	ns
Turn-On Rise Time		t _R			150	180	ns
Turn-Off Delay Time		t _{D(OFF)}			380	410	ns
Turn-Off Fall Time		t _F			180	220	ns
Total Gate Charge		Q _G	V _{DS} =520V, I _D =7A, V _{GS} =10V (Note 1, 2)		29	38	nC
Gate-Source Charge		Q _{GS}			9		nC
Gate-Drain Charge		Q _{GD}			19		nC
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS							
Drain-Source Diode Forward Voltage		V _{SD}	V _{GS} =0V, I _S = 7A			1.4	V
Maximum Continuous Drain-Source Diode Forward Current		I _S				7	A
Maximum Pulsed Drain-Source Diode Forward Current		I _{SM}				28	A
Reverse Recovery Time		t _{rr}	V _{GS} =0V, I _S =7.0A,		490		ns
Reverse Recovery Charge		Q _{RR}	dI _F /dt =100 A/μs (Note 1)		3.2		μC

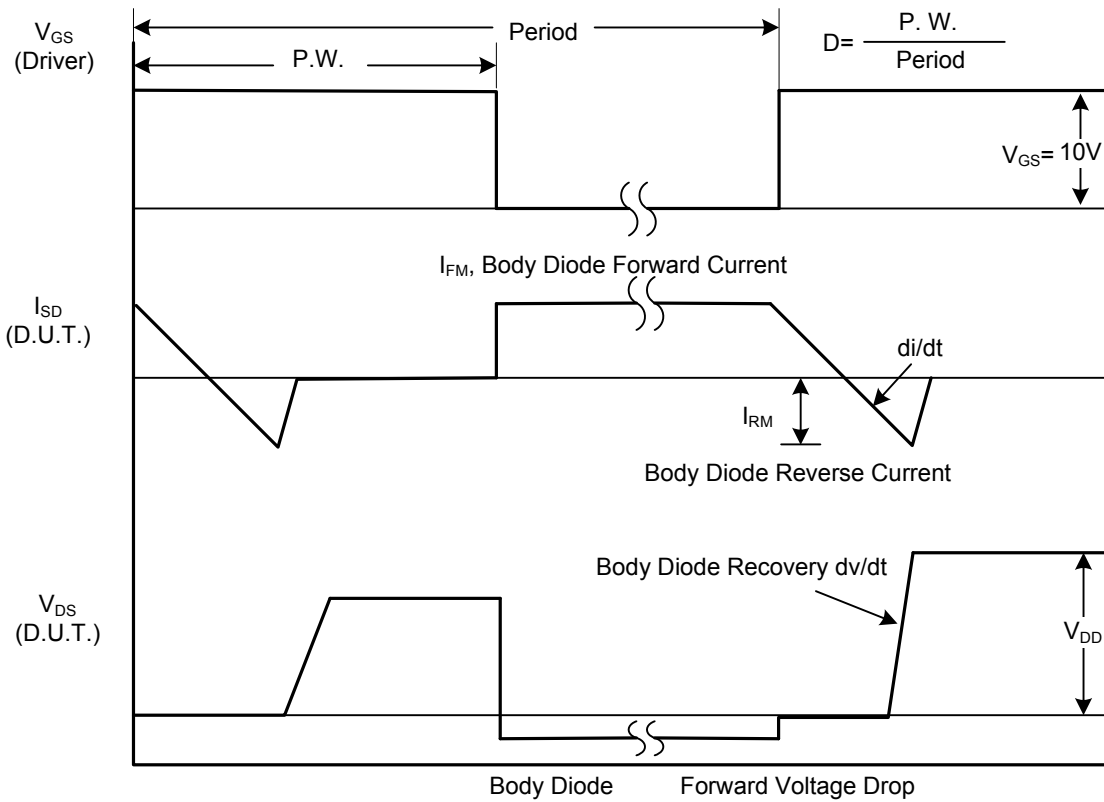
Notes: 1. Pulse Test: Pulse width ≤ 300μs, Duty cycle ≤ 2%.

2. Essentially independent of operating temperature.

TEST CIRCUITS AND WAVEFORMS

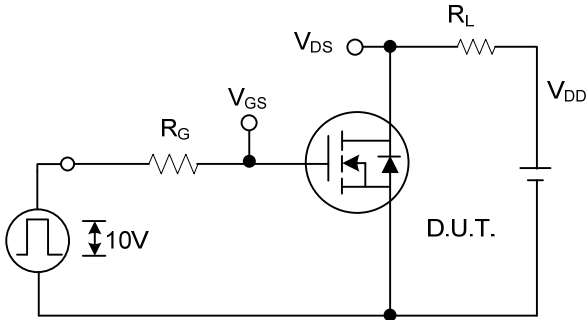


Peak Diode Recovery dv/dt Test Circuit

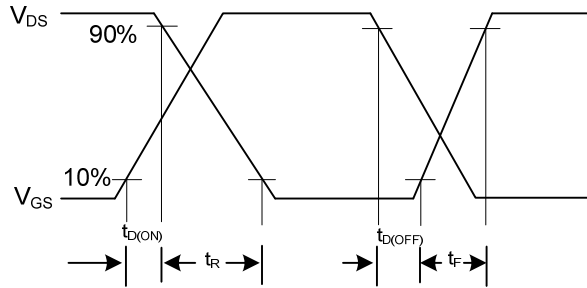


Peak Diode Recovery dv/dt Waveforms

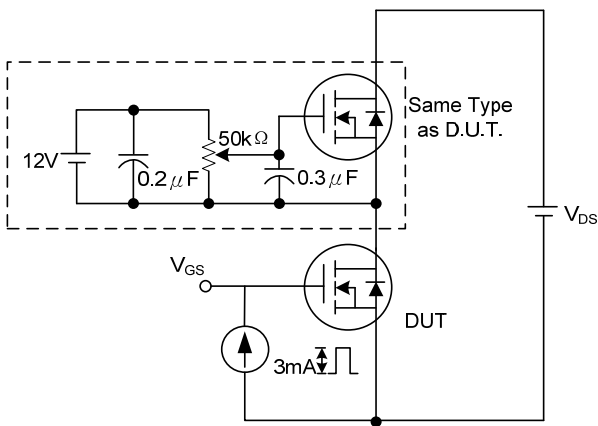
TEST CIRCUITS AND WAVEFORMS(Cont.)



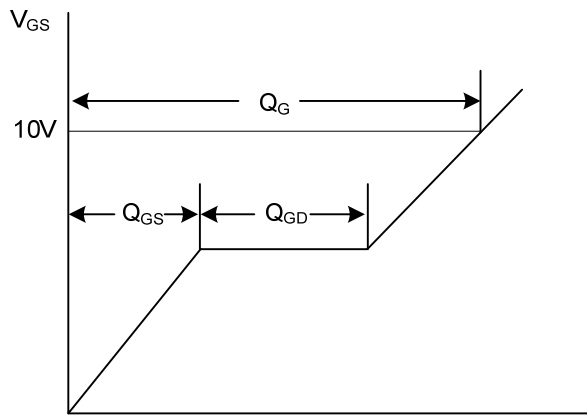
Switching Test Circuit



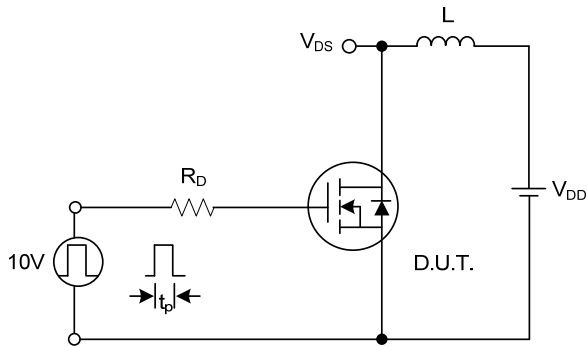
Switching Waveforms



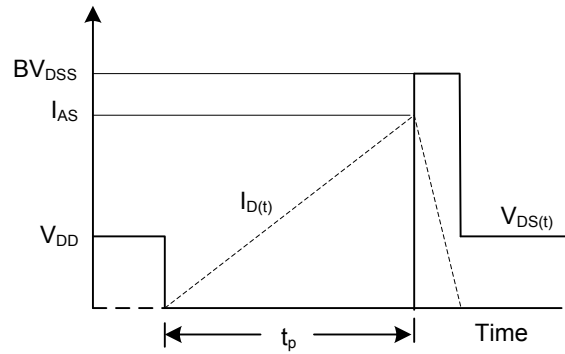
Gate Charge Test Circuit



Charge
Gate Charge Waveform



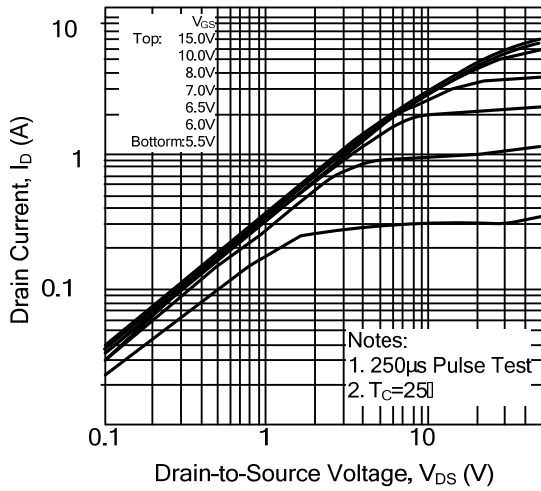
Unclamped Inductive Switching Test Circuit



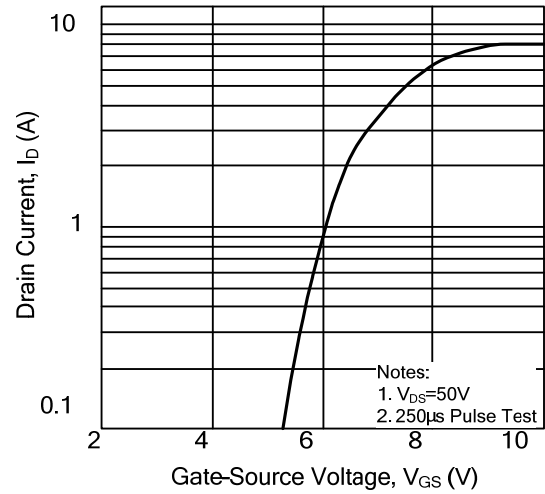
Unclamped Inductive Switching Waveforms

TYPICAL CHARACTERISTICS

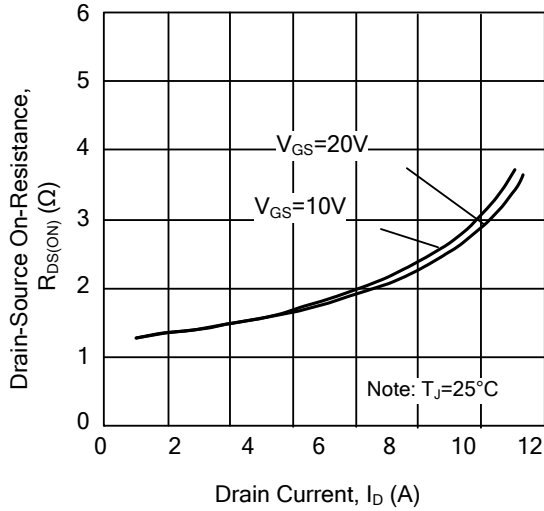
On-State Characteristics



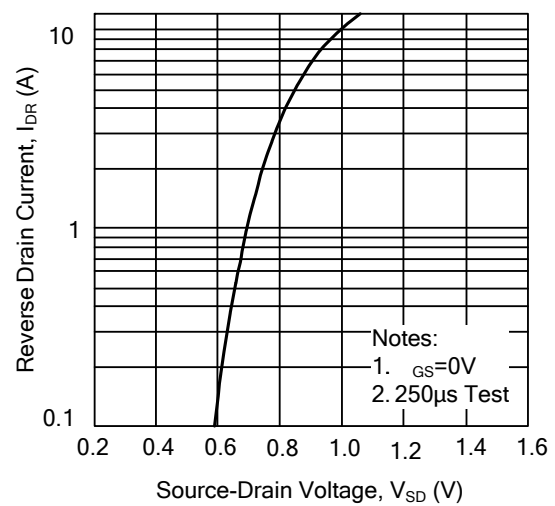
Transfer Characteristics



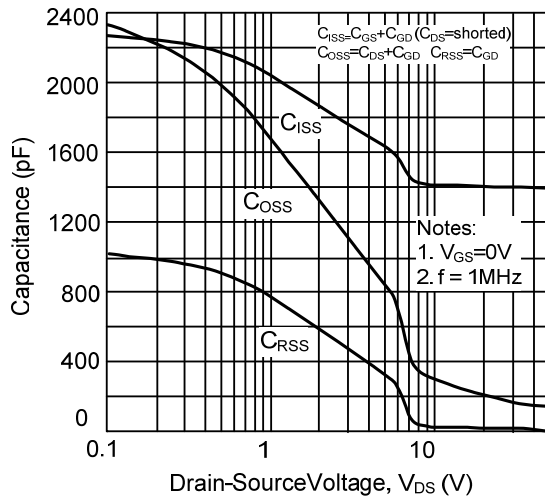
On-Resistance Variation vs. Drain Current and Gate Voltage



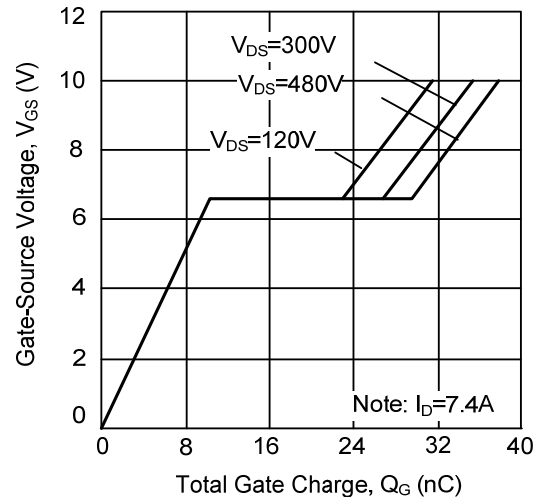
On State Current vs. Allowable Case Temperature



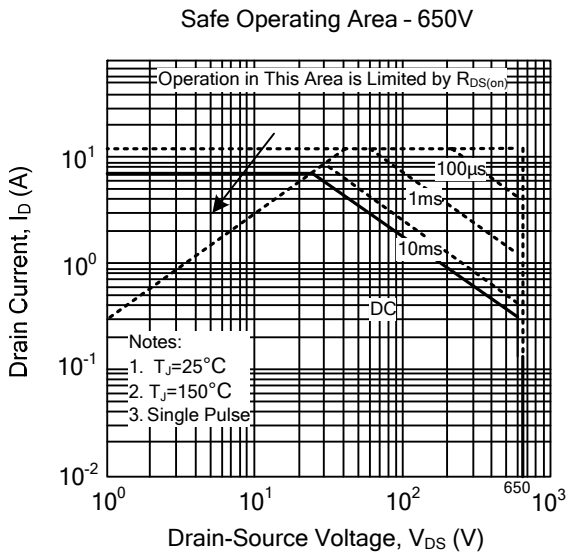
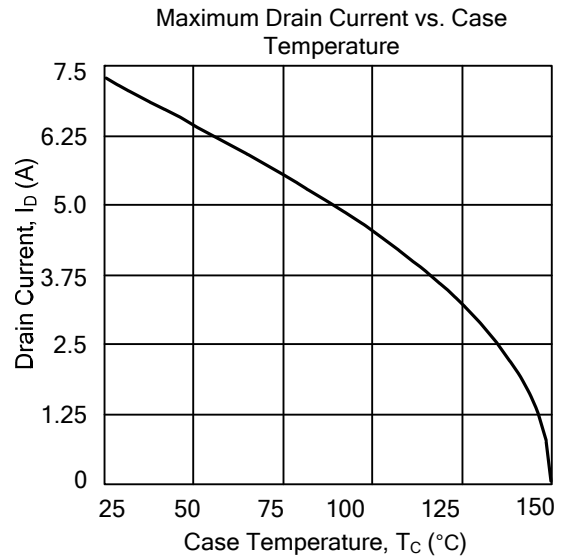
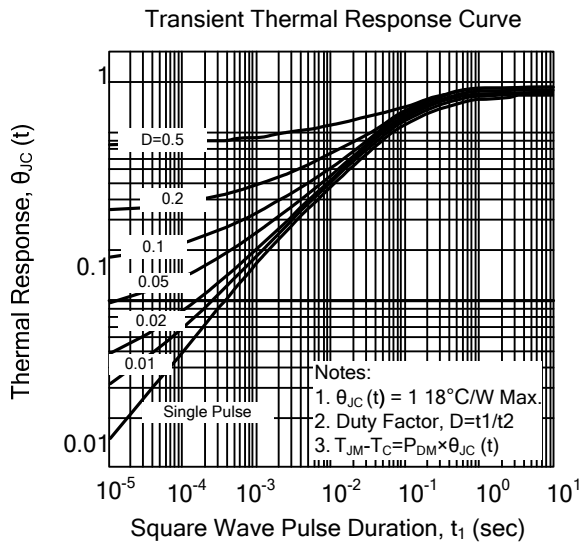
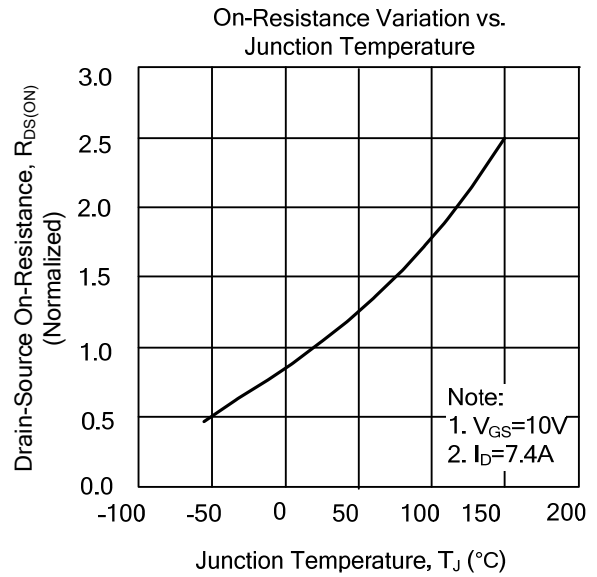
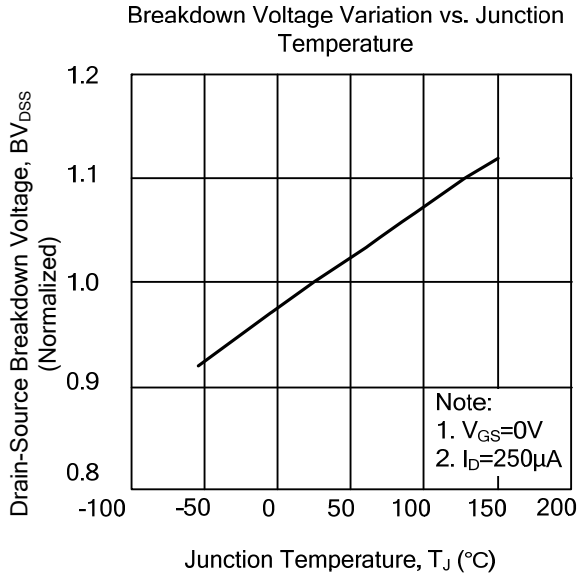
Capacitance Characteristics (Non-Repetitive)



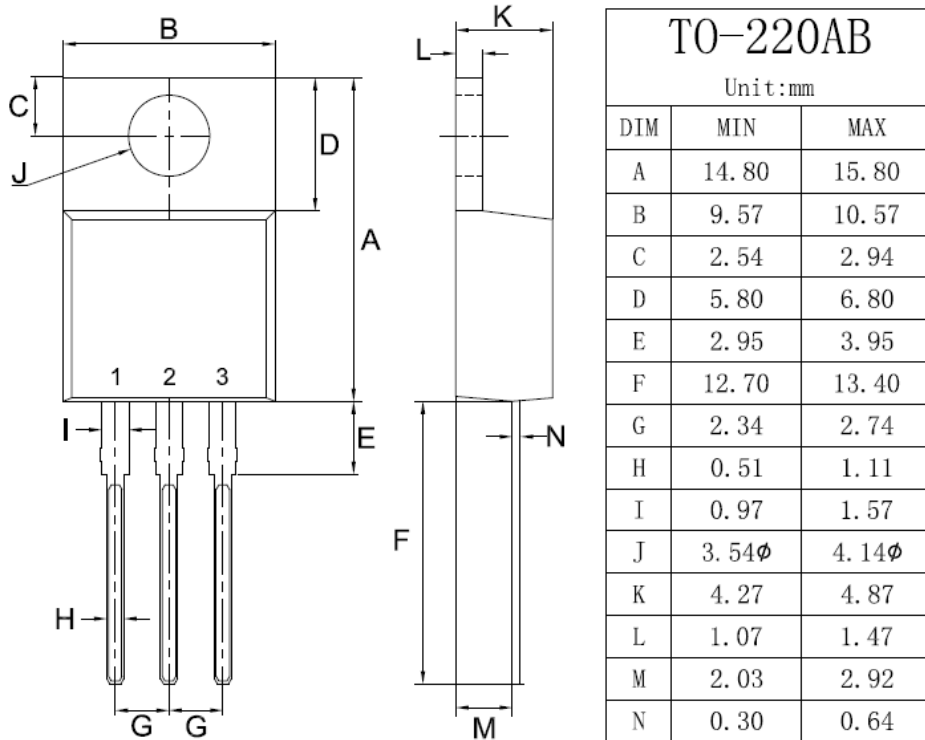
Gate Charge Characteristics



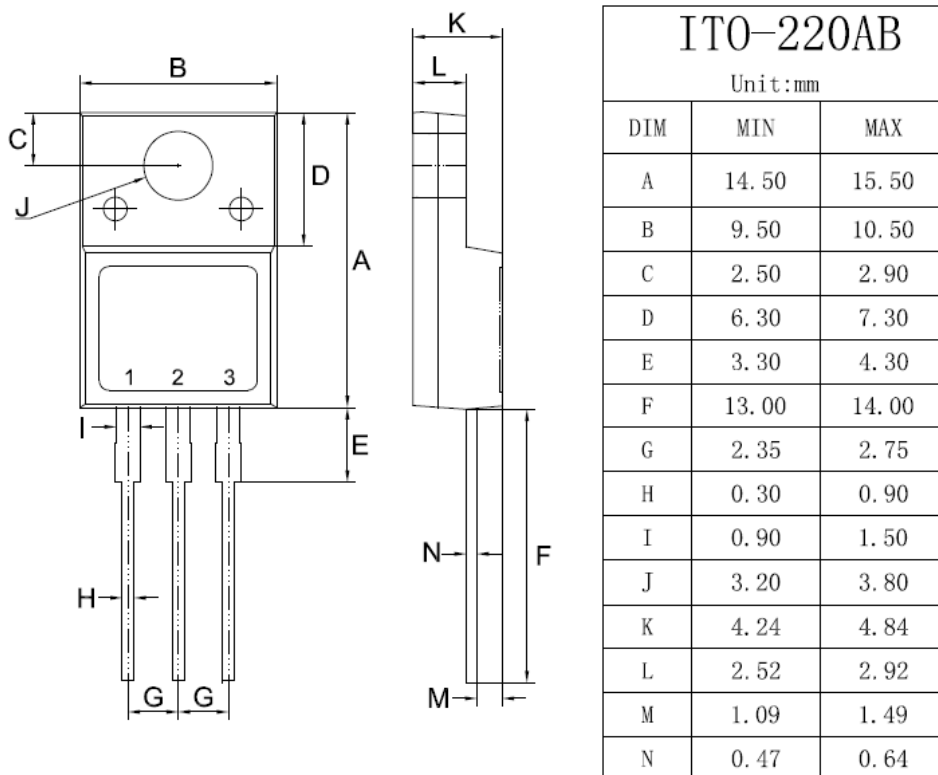
TYPICAL CHARACTERISTICS



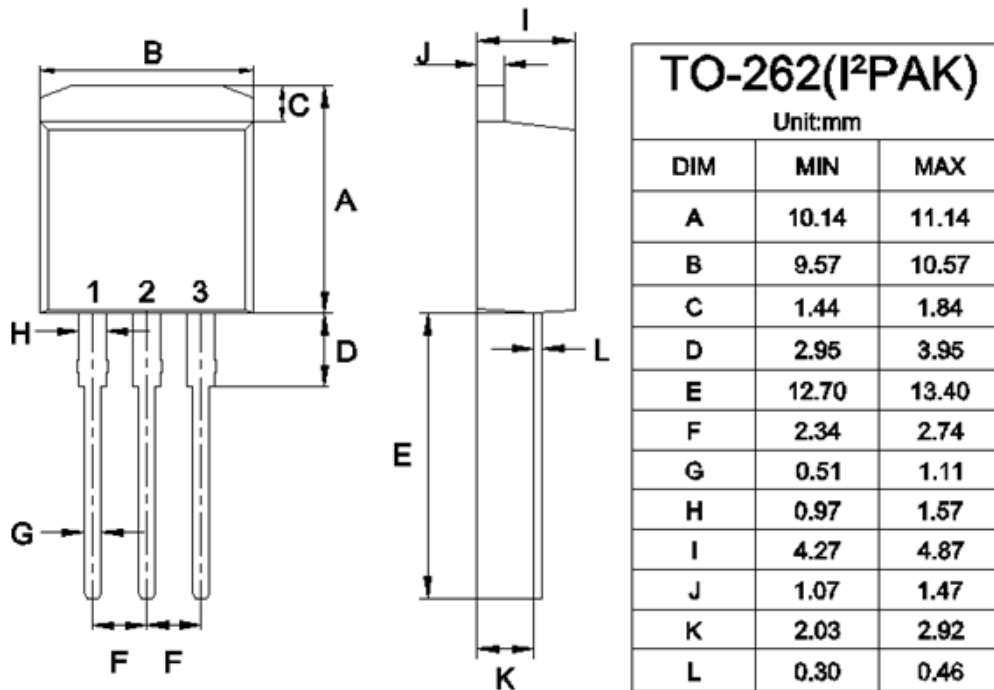
TO-220 Mechanical Drawing



ITO-220 Mechanical Drawing



TO-262 Mechanical Drawing



TO-263 Mechanical Drawing

